

Figure 1

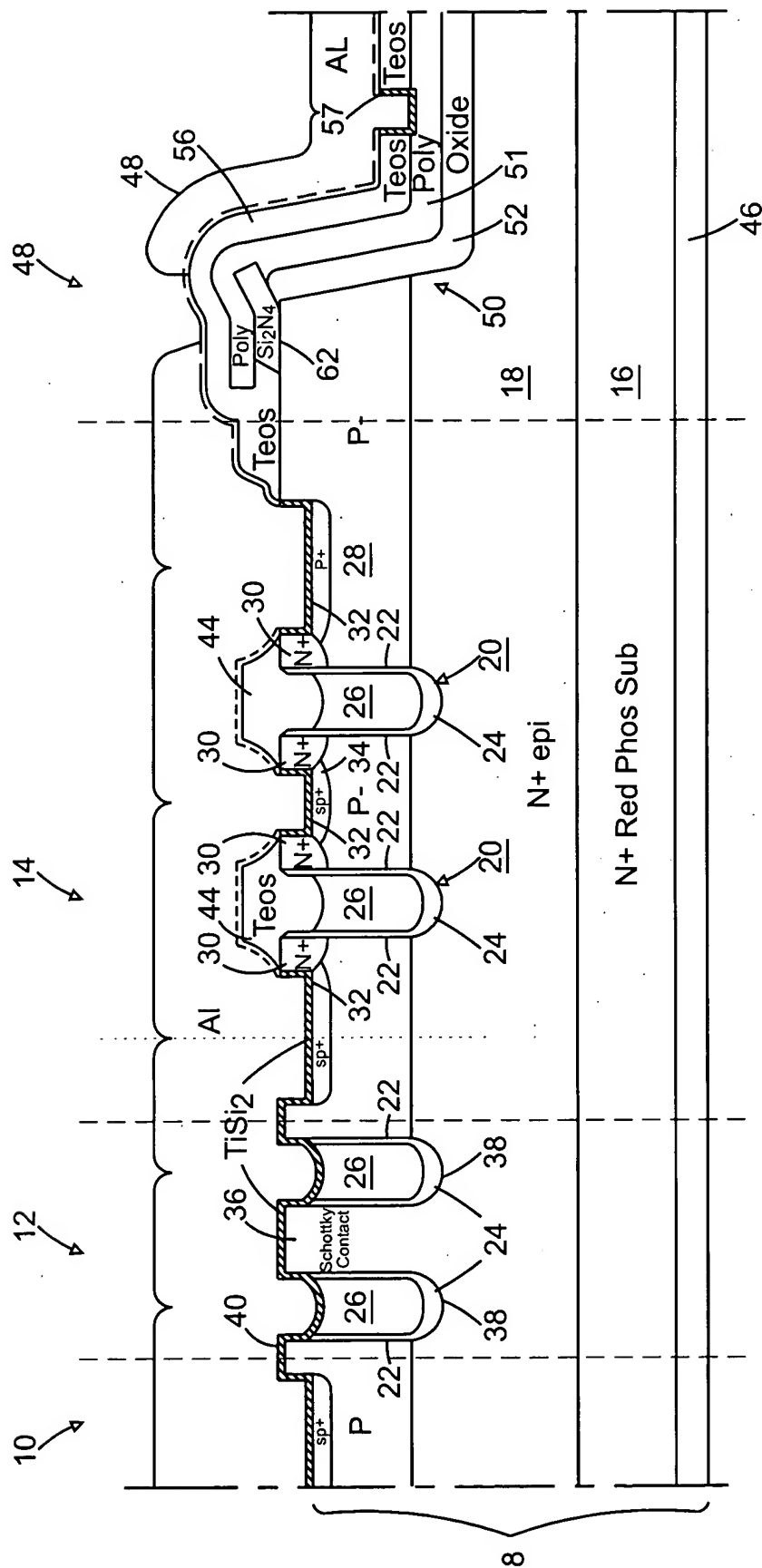


Figure 2



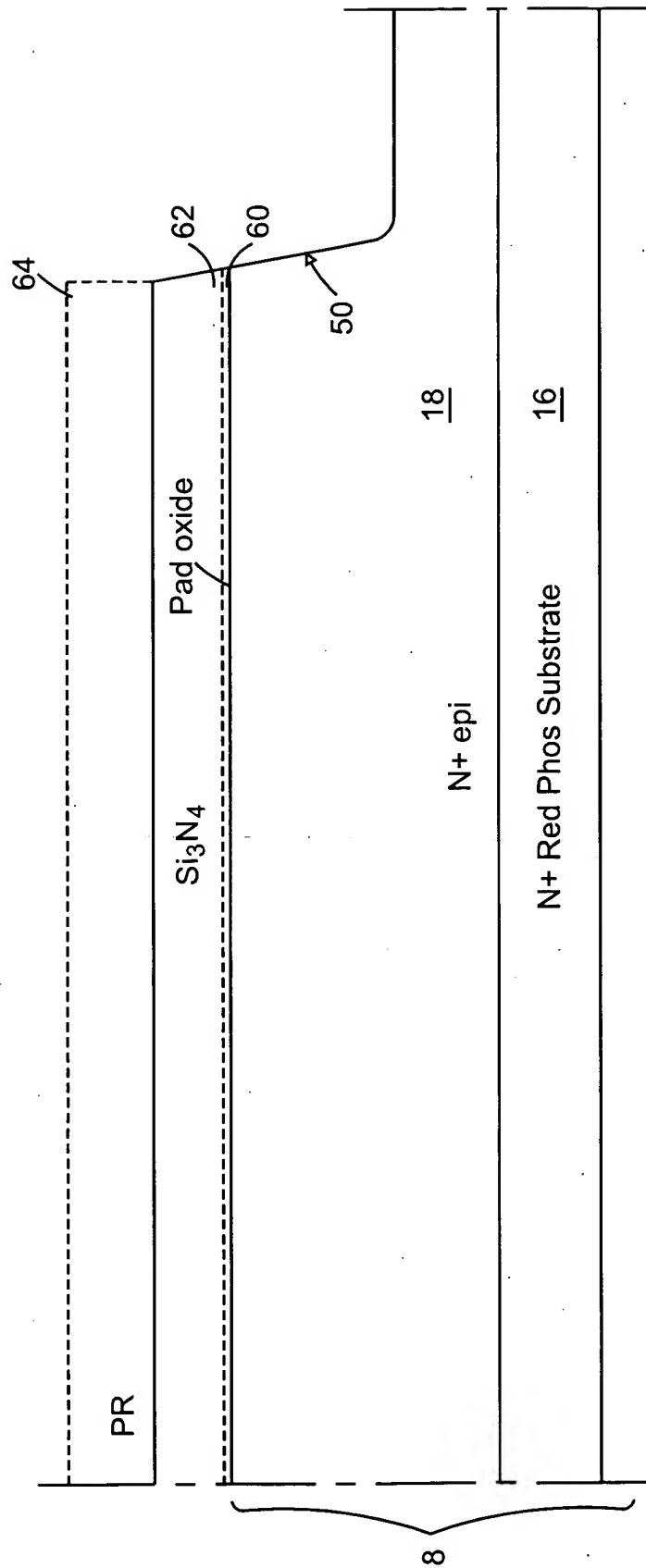


Figure 3



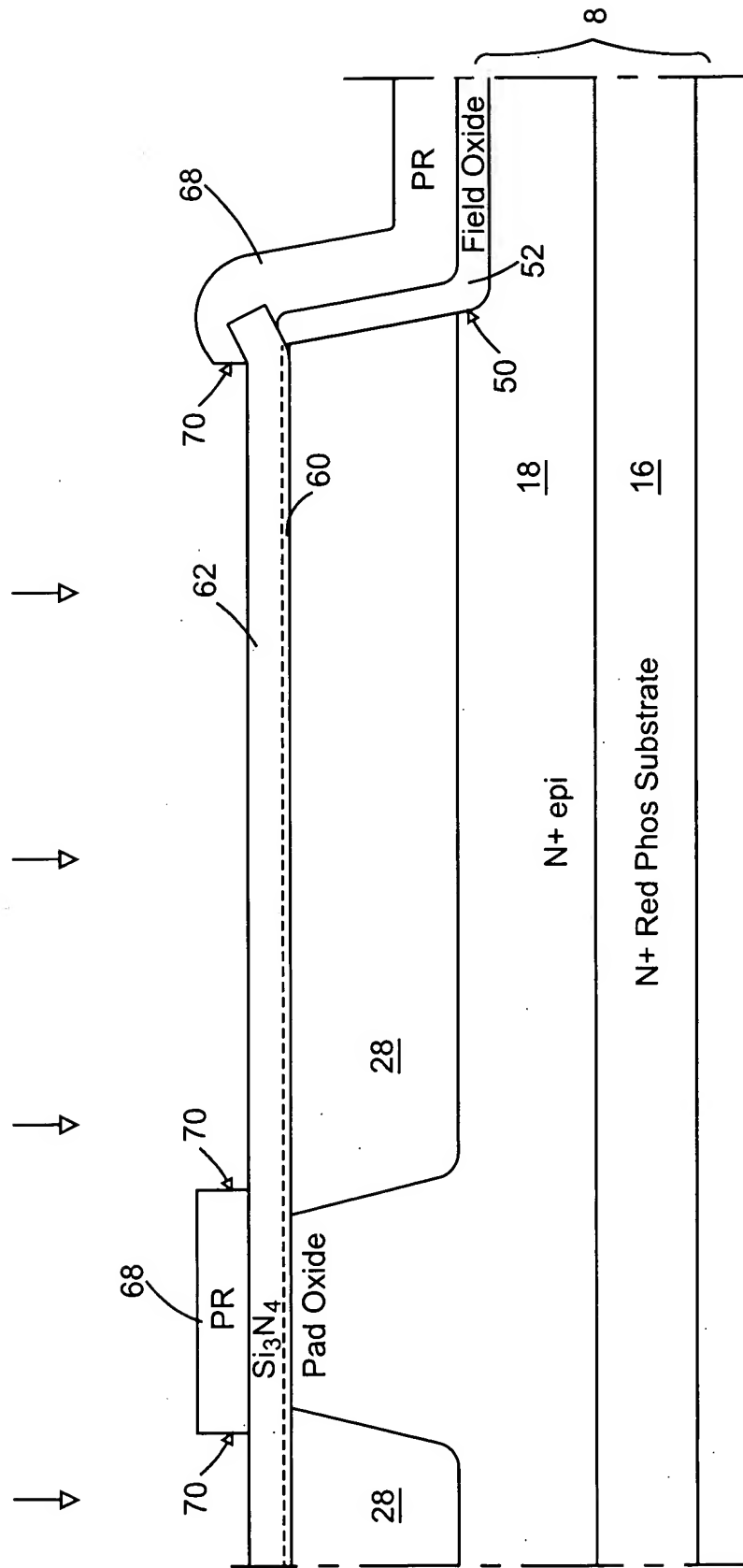


Figure 4



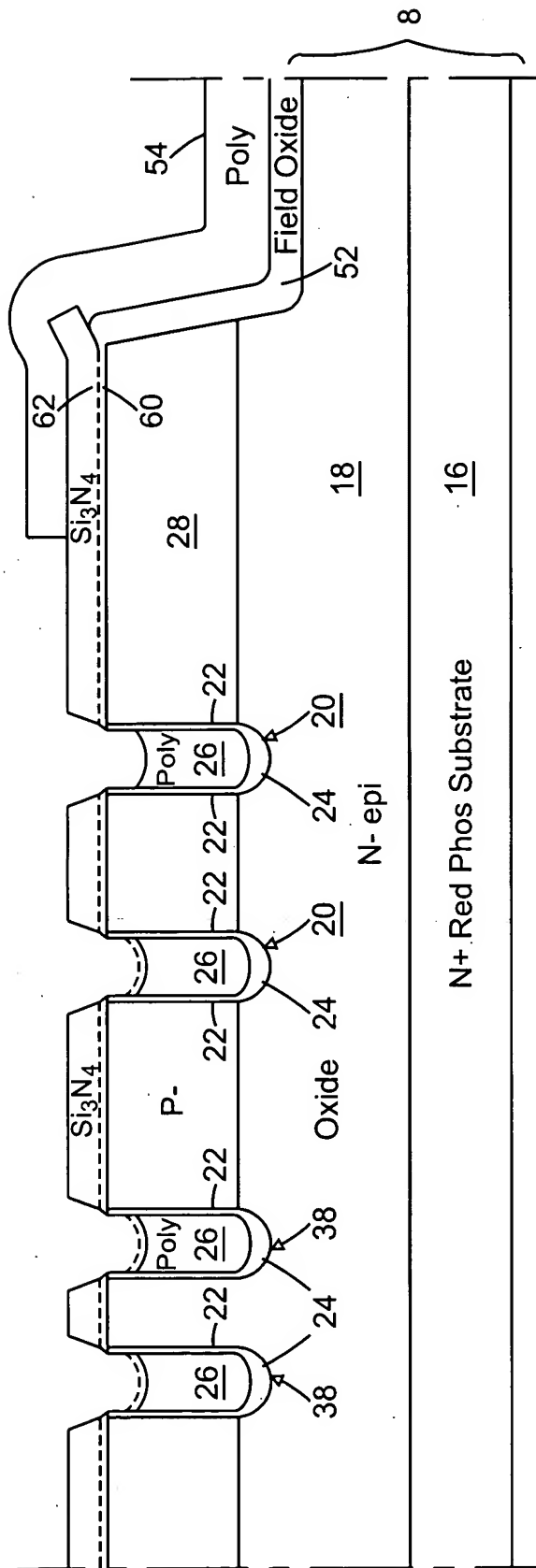


Figure 5







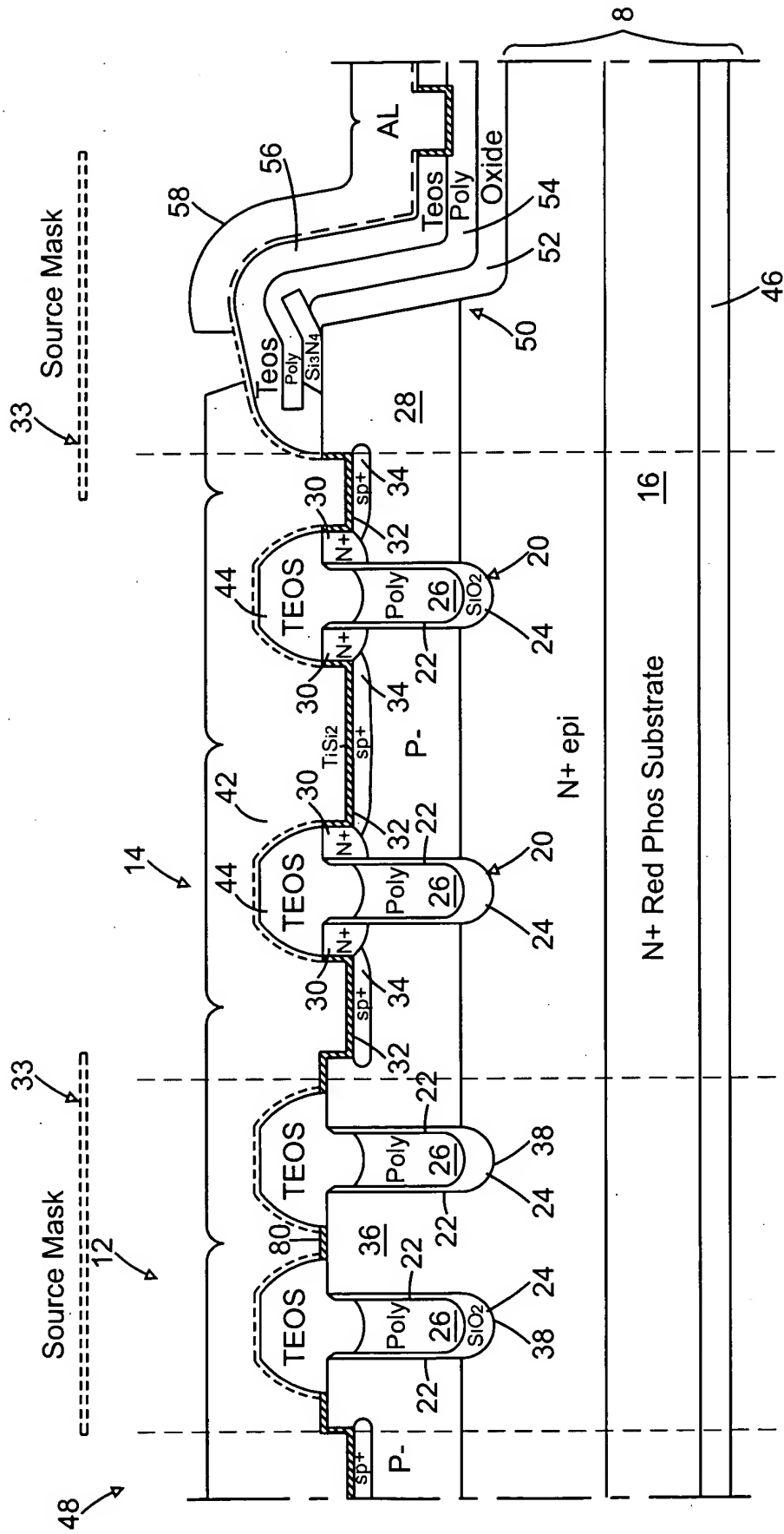


Figure 8





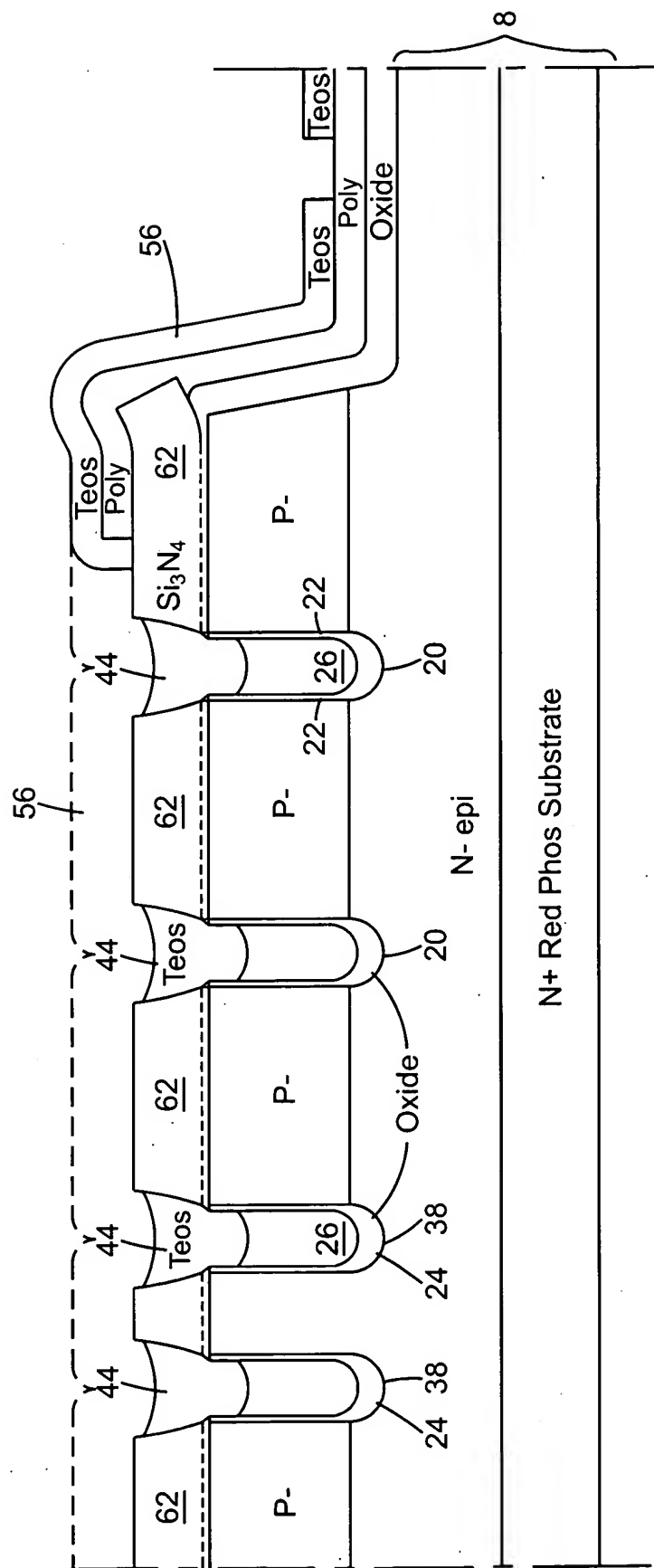
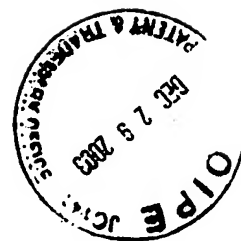


Figure 9





## Figure 10

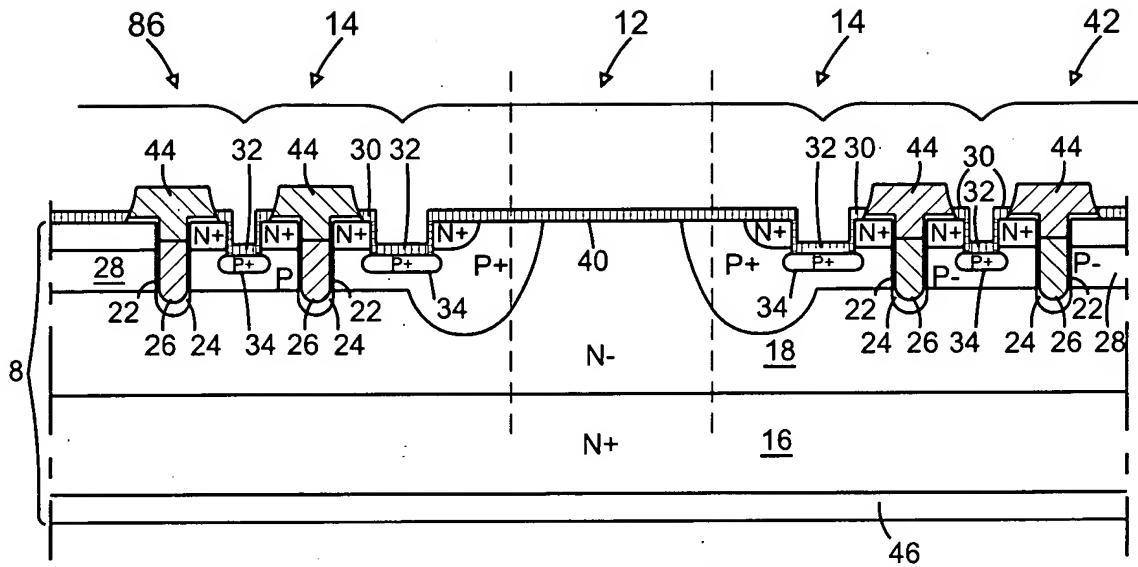
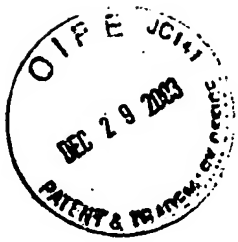


Figure 11

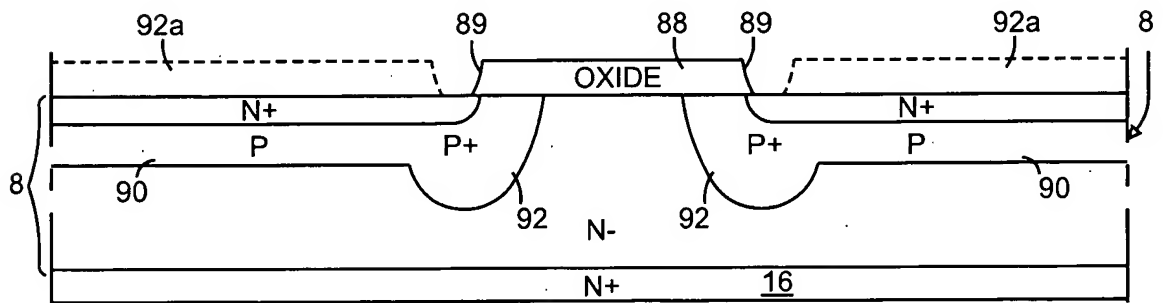
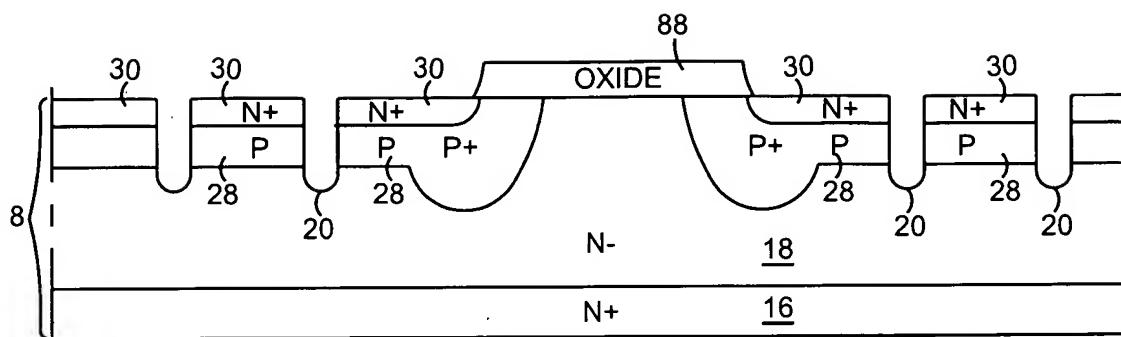


Figure 12

[illegible]

A cross-sectional view of a semiconductor device. The substrate consists of an N- region (18) and an N+ region (16). A top layer (8) contains oxide and poly regions. The device features two main sections, each with a central N+ region (32) and P+ regions (34). The top layer includes N+ regions (44) and P+ regions (98). The oxide layer is labeled OXIDE and the poly layer is labeled POLY. Various components are labeled with numbers 8, 16, 18, 32, 34, 44, 96, 98, and letters P, P+, N+, N-.

Figure 15